


**INPUT RECTIFIER DIODE**

	$V_F < 1.1V @ 40A$ $I_{FSM} = 475A$ $V_{RRM} = 800 - 1200V$
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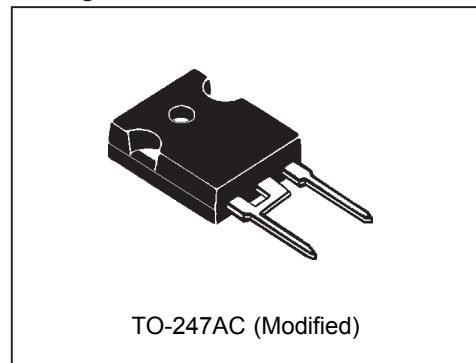
**Description/Features**

The 40EPS.. rectifier **SAFEIR** series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150° C junction temperature. Typical applications are in input rectification and these products are designed to be used with International Rectifier Switches and Output Rectifiers which are available in identical package outlines.

**Major Ratings and Characteristics**

Characteristics	Values	Units
$I_{F(AV)}$ Sinusoidal waveform	40	A
$V_{RRM}$ Range (*)	800- 1200	V
$I_{FSM}$	475	A
$V_F$ @40A, $T_J=25^{\circ}C$	1.1	V
$T_J$	-40 to 150	°C

**Package Outline**



(\*) for higher voltage up to 1600V contact factory

## Voltage Ratings

Part Number	$V_{RRM}$ , maximum peak reverse voltage V	$V_{RSM}$ , maximum non repetitive peak reverse voltage V	$I_{RRM}$ 150°C mA
40EPS08	800	900	1
40EPS12	1200	1300	

## Absolute Maximum Ratings

Parameters	40EPS..	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current	40	A	@ $T_C = 105^\circ\text{C}$ , 180° conduction half sine wave
$I_{FSM}$ Max. Peak One Cycle Non-Repetitive Surge Current	400	A	10ms Sine pulse, rated $V_{RRM}$ applied
	475		10ms Sine pulse, no voltage reapplied
$I^2t$ Max. $I^2t$ for fusing	800	$A^2s$	10ms Sine pulse, rated $V_{RRM}$ applied
	1131		10ms Sine pulse, no voltage reapplied
$I^2vt$ Max. $I^2vt$ for fusing	11310	$A^2vs$	t = 0.1 to 10ms, no voltage reapplied

## Electrical Specifications

Parameters	40EPS..	Units	Conditions
$V_{FM}$ Max. Forward Voltage Drop	1.1	V	@ 40A, $T_J = 25^\circ\text{C}$
$r_t$ Forward slope resistance	7.16	$m\Omega$	$T_J = 150^\circ\text{C}$
$V_{F(TO)}$ Threshold voltage	0.74	V	
$I_{RM}$ Max. Reverse Leakage Current	0.1	mA	$T_J = 25^\circ\text{C}$
	1.0		$T_J = 150^\circ\text{C}$

$V_R = \text{rated } V_{RRM}$

## Thermal-Mechanical Specifications

Parameters	40EPS..	Units	Conditions
$T_J$ Max. Junction Temperature Range	-40 to 150	$^\circ\text{C}$	
$T_{stg}$ Max. Storage Temperature Range	-40 to 150	$^\circ\text{C}$	
$R_{thJC}$ Max. Thermal Resistance Junction to Case	0.6	$^\circ\text{C/W}$	DC operation
$R_{thJA}$ Max. Thermal Resistance Junction to Ambient	40	$^\circ\text{C/W}$	
$R_{thCS}$ Typical Thermal Resistance, Case to Heatsink	0.2	$^\circ\text{C/W}$	Mounting surface, smooth and greased
wt Approximate Weight	6(0.21)	g(oz.)	
T Mounting Torque	Min.	6(5)	$\text{Kg-cm}$ $(\text{lbf-in})$
	Max.	12(10)	
Case Style	TO-247AC		JEDEC (Modified)

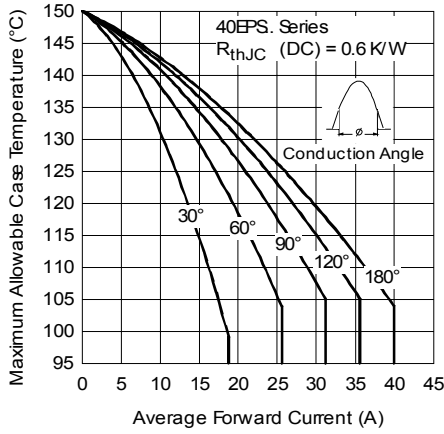


Fig. 1 - Current Rating Characteristics

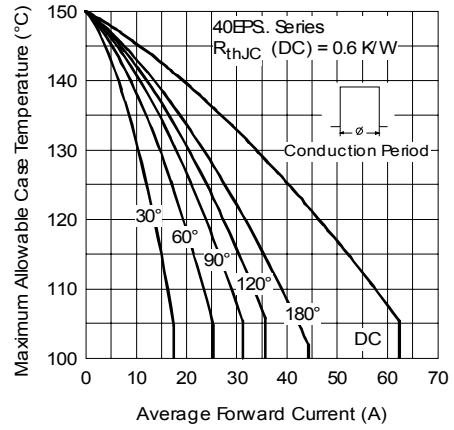


Fig. 2 - Current Rating Characteristics

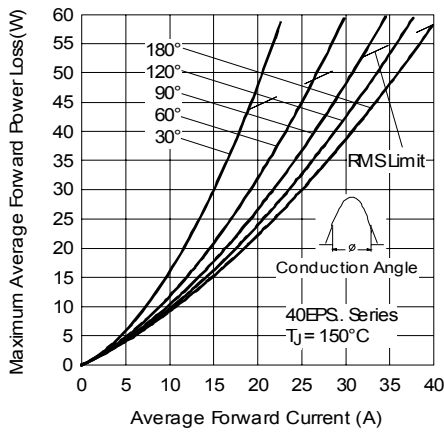


Fig. 3 - Forward Power Loss Characteristics

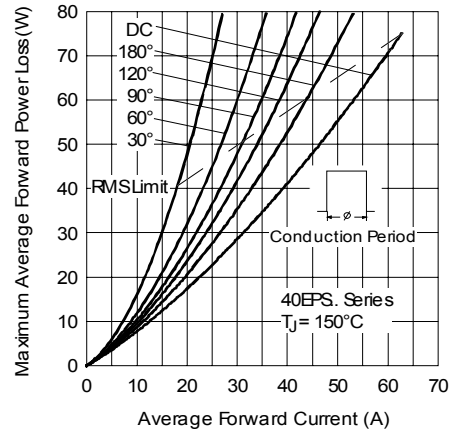


Fig. 4 - Forward Power Loss Characteristics

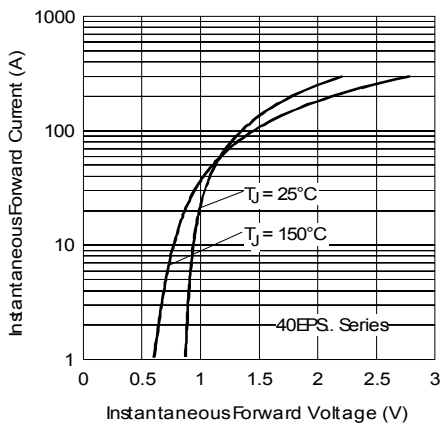


Fig. 5 - Forward Voltage Drop Characteristics

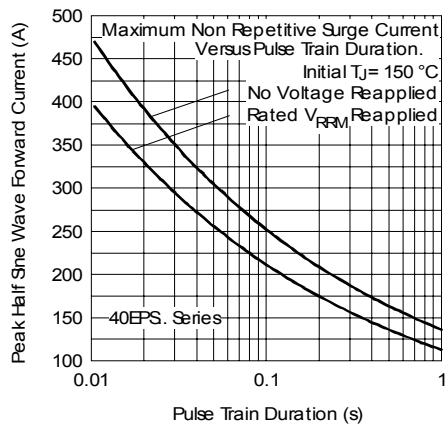


Fig. 6 - Maximum Non-Repetitive Surge Current

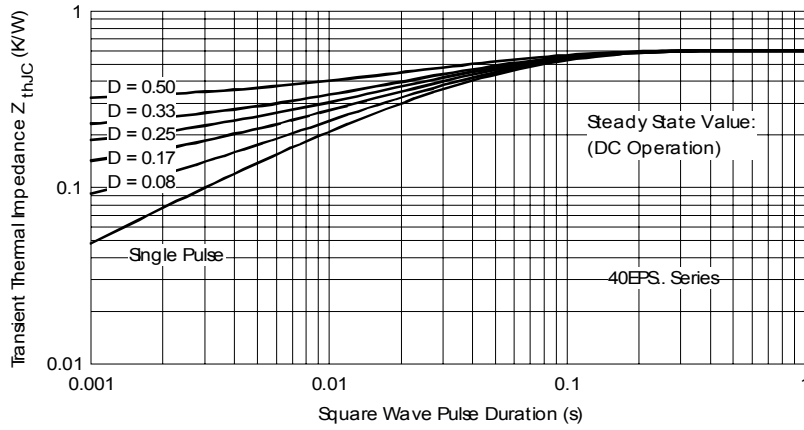
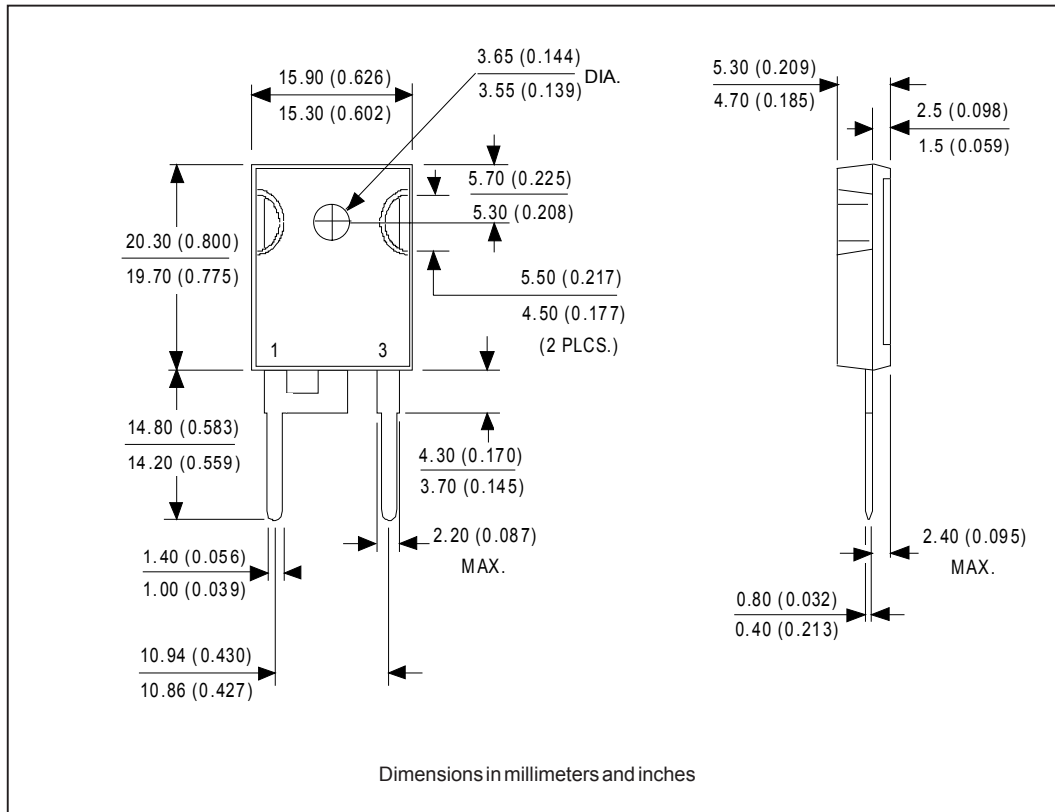


Fig. 7 - Thermal Impedance  $Z_{thJC}$  Characteristics

Outline Table



Marking Information

EXAMPLE: THIS IS A 40EPS12 WITH ASSEMBLY LOT CODE 5657 ASSEMBLED ON WW 35, 2000 IN THE ASSEMBLY LINE "H"

INTERNATIONAL RECTIFIER LOGO  
 ASSEMBLY LOT CODE  
 PART NUMBER  
 DATE CODE  
 YEAR 0 = 2000  
 WEEK 35  
 LINE H

Ordering Information Table

**Device Code**

40	E	P	S	12
①	②	③	④	⑤

- 1** - Current Rating (40 = 40A)
- 2** - Circuit Configuration  
E = Single Diode
- 3** - Package  
P = TO-247AC (Modified)
- 4** - Type of Silicon  
S = Standard Recovery Rectifier
- 5** - Voltage code: Code x 100 =  $V_{RRM}$

08 = 800V  
 12 = 1200V

Data and specifications subject to change without notice.  
 This product has been designed and qualified for Industrial Level.  
 Qualification Standards can be found on IR's Web site.